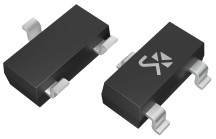
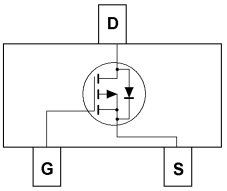
P-Channel Enhancement Mode MOSFET

-30V_{DS}/ ±20V_{GS}/ -4.1A I_D

Feature

- -30V/-4.1A, $R_{DS(ON)}$ =51mΩ(MAX) @V_{GS} = -10V.
  $R_{DS(ON)}$ = 68mΩ(MAX) @V_{GS} = -4.5V.





SOT-23

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings T_A=25℃Unless Otherwise noted

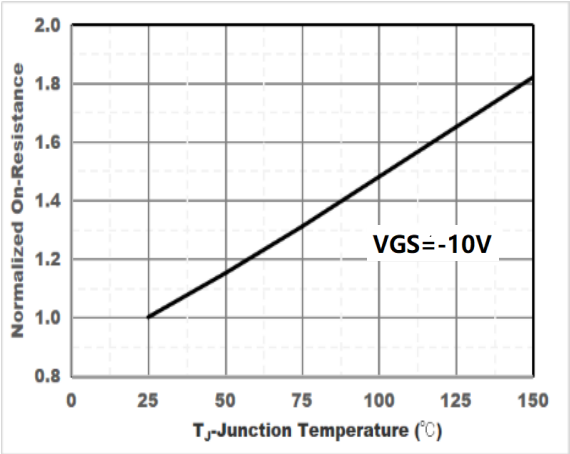
Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-4.1	A

Electrical Characteristics T_A=25℃Unless Otherwise noted

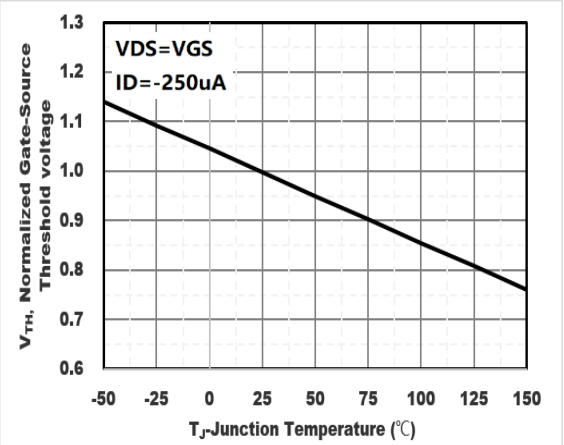
Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-30	-33	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=-30V, VGS=0V	-	-	-0.3	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=20V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-20V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-1.0	-1.5	-2.4	V
Static Drain-source On-Resistance	RDS(ON)	VGS =-10V, ID =-4.1A	-	36	51	mΩ
		VGS =-4.5V, ID =-3.5A	-	52	68	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.0A			-1.2	V

Typical Characteristics

$R_{DS(ON)}$ vs Junction Temperature



$V_{GS(th)}$ vs Junction Temperature



Package Outline Dimensions (UNIT: mm) SOT-23